

1.1 Scope.

This specification covers the requirements for a CMOS monolithic address generator.

1.2 Part Number.

The complete part number per Table 1 of this specification is as follows:

Device	Part Number
-1	ADSP-1410SD/883B
-2	ADSP-1410TD/883B

1.2.3 Case Outline.

See Appendix 1 of General Specification ADI-M-1000: package outline: D-48A.

1.3 Absolute Maximum Ratings.

Supply Voltage	-0.3V to 7V
Input Voltage	-0.3V to V_{DD}
Output Voltage	-0.3V to V_{DD}
Operating Temperature Range (Ambient)	-55°C to +125°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering 10sec)	+300°C

1.5 Thermal Characteristics.

Thermal Resistance θ_{JC} : see MIL-M-38510, Appendix C.

ADSP-1410 – SPECIFICATIONS

Parameter	Symbol	Device	Design Limit @ +25°C	Sub Group 1	Sub Group 2, 3	Sub Group 9	Sub Group 10, 11	Test Condition ¹	Units
Digital Input High Voltage	V _{IH}	-1, 2	2.0	2.0	2.0			V _{DD} = max	V min
Clock Input High Voltage*	V _{IHC}	-1, 2	3.0	3.5	3.5			V _{DD} = max	V min
Digital Input Low Voltage	V _{IL}	-1, 2	0.8	0.8	0.8			V _{DD} = min	V max
Digital Output High Voltage	V _{OH}	-1, 2	2.4	2.4	2.4			V _{DD} = min I _{OH} = -1mA	V min
Digital Output Low Voltage*	V _{OL}	-1, 2	0.4	0.6	0.6			V _{DD} = min I _{OL} = +3mA	V max
Digital Input High Current	I _{IH}	-1, 2	10	10	10			V _{DD} = max V _{IN} = +5.0V	μA max
Digital Input Low Current	I _{IL}	-1, 2	10	10	10			V _{DD} = max V _{IN} = 0.0V	μA max
Three-State Leakage Current Low	I _{OZL}	-1, 2	50	50	50			V _{DD} = max V _{IN} = 0V (High Z)	μA max
Three-State Leakage Current High	I _{OZH}	-1, 2	50	50	50			V _{DD} = max V _{IN} = max (High Z)	μA max
Supply Current*	I _{DD1}	-1, 2	75	100	100			V _{DD} = max; TTL Inputs; f = max	mA max
	I _{DD2}	-1, 2	35	50	50			All V _{IN} = 2.4V	mA max
Instruction Setup Time*	t _{IS}	-1	20			30	30	Note 2	ns min
		-2	15			20	20		
Instruction Hold Time*	t _{IH}	-1	5			5	5	Note 2	ns min
		-2	4			4	4		
Instruction Cycle Time*	t _{CY}	-1	100			125	125	Note 2	ns min
		-2	90			100	100		
Input Data Setup Time	t _{IDS}	-1, 2	10			10	10	Note 2	ns min
Input Data Hold Time*	t _{IDH}	-1, 2	5			6	6	Note 2	ns min
Guaranteed Clock-to-Data Delay*	t _{ODD}	-1	35			45	45	Notes 2, 3	ns min
		-2	30			40	40		
		-1	55			70	70		ns max
		-2	50			60	60		
Output Data Disable Time*	t _{DDIS}	-1	20			25	25	Note 2	ns max
		-2	20			20	20		
Output Address Disable Time* (Latched Mode)	t _{ADISL}	-1	30			45	45	Note 2	ns max
		-2	25			40	40		
Output Address Disable Time* (Transparent Mode)	t _{ADIST}	-1	40			55	55	Note 2	ns max
		-2	35			50	50		
LATCHED MODE, GUARANTEED CLOCK-TO-OUTPUT DELAYS									
Pre-Update Address Delay*	t _{LAN}	-1	35			40	40	Notes 2, 3	ns min
		-2	30			35	35		
		-1	45			55	55		ns max
		-2	35			45	45		
Pre-Update CMP/Z Flag Delay*	t _{LFN}	-1	45			60	60	Notes 2, 3; C = 25pF	ns min
		-2	35			45	45		
		-1	55			75	75		ns max
		-2	45			60	60		

Table 1. (Continued on next page)

REV. B

Parameter	Symbol	Device	Design Limit @ +25°C	Sub Group 1	Sub Group 2, 3	Sub Group 9	Sub Group 10, 11	Test Condition ¹	Units
Output Data Enable Time	t _{DENA}	-1	30			40	40	Notes 2, 4	ns min
		-2	25			35	35		
		-1	50			65	65	Notes 2, 4	ns max
		-2	45			55	55		
Post-Update Address Delay*	t _{LAP}	-1	35			40	40	Notes 2, 3	ns min
		-2	30			35	35		
		-1	60			75	75	Notes 2, 4	ns max
		-2	50			55	55		
Post-Update CMP/Z Flag Delay*	t _{LFP}	-1	45			60	60	Notes 2, 3; C = 25pF	ns min
		-2	35			45	45		
		-1	70			95	95		ns max
		-2	55			75	75		
TRANSPARENT MODE, VALID-INSTRUCTION-TO-OUTPUT DELAYS									
Pre-Update Address Delay*	t _{TAN}	-1	50			65	65	Note 2	ns max
		-2	45			55	55		
Pre-Update CMP/Z Flag Delay*	t _{TFN}	-1	65			90	90	Note 2; C = 25pF	ns max
		-2	55			70	70		
Post-Update Address Delay*	t _{TAP}	-1	75			95	95	Note 2	ns max
		-2	65			80	80		
Post-Update CMP/Z Flag Delay**	t _{TFP}	-1	90			115	115	Note 2; C = 25pF	ns max
		-2	75			95	95		
SUPPLEMENTAL PARAMETERS FOR DOUBLE-CHIP/DOUBLE-PRECISION OPERATIONS⁵									
Valid Instruction to Carry/Shift Output Delay*	t _{CSD}	-1	65			80	80	Note 2	ns max
		-2	57			72	72		
Carry/Shift Input Setup Time*	t _{CSS}	-1	35			40	40	Note 2	ns min
		-2	28			35	35		
Carry/Shift Input to Valid MS Address (Post-Update Only)*	t _{MSD}	-1	45			55	55	Note 2	ns max
		-2	40			48	48		
Valid Instruction to MS CMP/Z Flag Delay	t _{CZD_C}	-1	115			120	120	Note 2	ns max
		-2	105			115	115		
Clock High to CMP/Z (Compare) Invalid Delay	t _{CZI}	-1, 2	4			4	4	Note 2	ns min
Valid Instruction to CMP/Z (Zero) Flag Delay	t _{CZD_Z}	-1	80			85	85	Note 2	ns max
		-2	70			80	80		
Instruction Valid to CMP/Z (Zero) Invalid Delay	t _{IID}	-1, 2	10			10	10	Note 2	ns min

NOTES

*Indicates that a limit for this parameter has changed from REV. A.

¹T_A = +25°C; V_{DD} = +4.5V min to +5.5V max (unless otherwise noted).

²Input levels are GND and +3.0V; V_{DD} = +4.5V. Rise times are 5ns. Input timing reference levels and output reference levels are measured at +1.5V per Figure 1.

³Measured with the maximum usable instruction setup time before the rising edge of the clock. This max usable setup time may be calculated for any timing spec as:

Maximum usable instruction setup time = max(t_{SPEC}) - min(t_{SPEC}) + min(t_{IS}). For example, Maximum usable setup time for t_{LAN} for the -2 part is:

max(t_{LAN}) - min(t_{LAN}) + min(t_{IS}) = 45 - 35 + 20 = 30ns.

⁴Measured with the minimum instruction setup time for the respective -1 or -2 part.

⁵The Instruction Cycle Time, t_{CY}, does not apply to DCDP operation. Clock HI and LO relationships for DCDP operation are described in the text below under DCDP Parameters: t_{HI} is derived from the t_{CSD}, t_{CSS}, t_{MSD} and t_{IS} parameters, and the inequality t_{L0} ≥ t_{IS} must also hold.

Table 1.

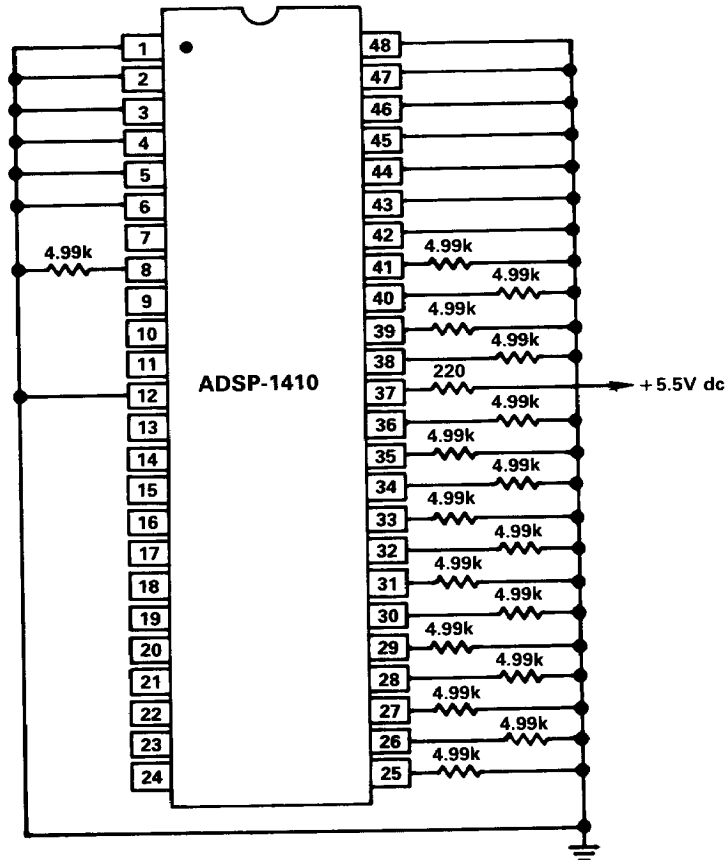
REV. B

3.2.4 Microcircuit Technology Group.

This microcircuit is covered by technology group (105).

4.2.1 Life Test/Burn-In Circuit.

Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).



ADSP-1410

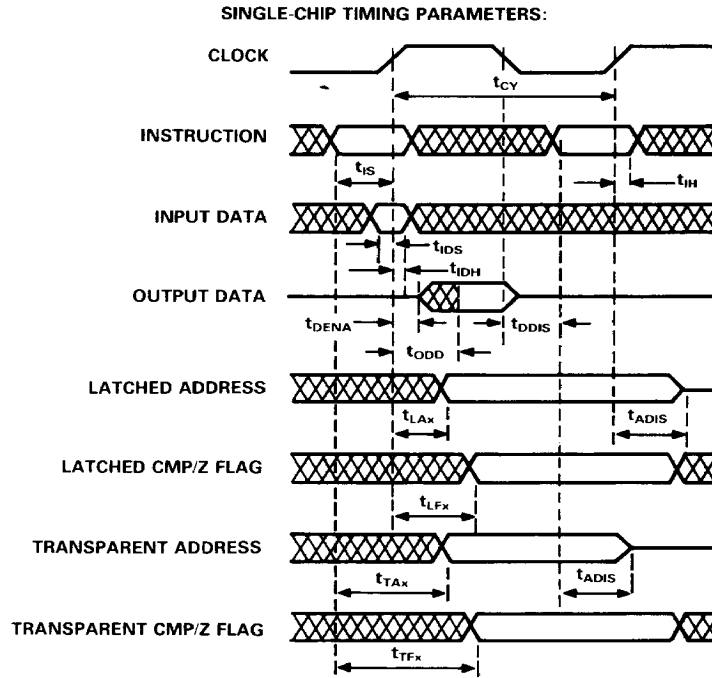


Figure 1. ADSP-1410 Timing Diagram

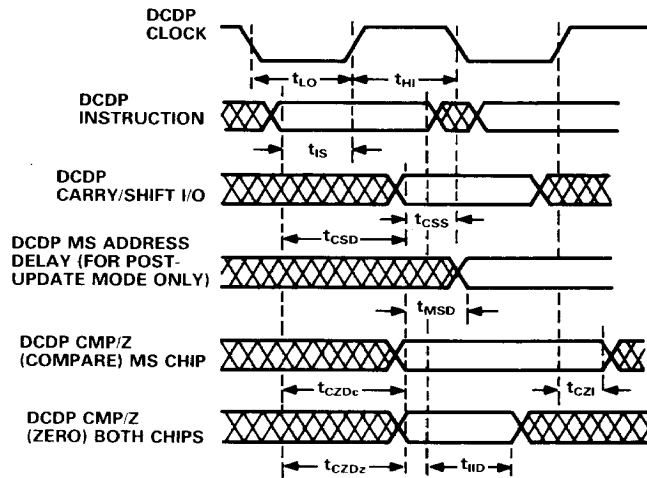


Figure 2. Supplemental Parameters for Double-Chip/Double-Precision Operation

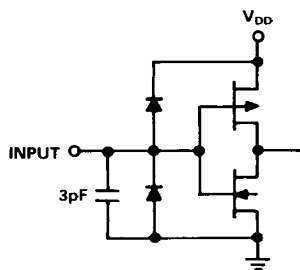


Figure 3. Equivalent Input Circuit

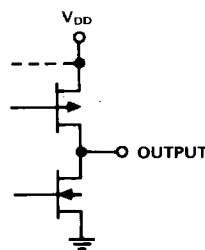


Figure 4. Equivalent Output Circuits

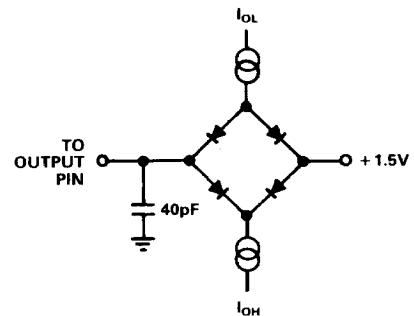


Figure 5. Normal Load for AC Measurements

Instr.	Opcode (I ₉₋₀)	Description
Looping Instructions		
YINC*†:	1011ccrrrr	output & increment/init
YDEC*†:	1010ccrrrr	output & decrement/init
YADD*†:	11ccbbllrrr	output & add offset/init
YSUB*†:	11ccbb0rrr	output & subtract offset/init
Register Transfer Instructions		
YRTR*:	000101rrrr	output & xfr R to R
YRTB*:	0011bbrrrr	output & xfr R to B
YRTC*:	0010ccrrrr	output & xfr R to C
DTI:	00001111ii	xfr D to I
ITR:	1000iirrrr	xfr I to R
BTR:	0100bbrrrr	xfr B to R
RTD:	000100rrrr	xfr R to D
CTD:	00001100cc	xfr C to D
BTD:	00001101bb	xfr B to D
ITD:	00001110ii	xfr I to D
Logical and Shift Instructions		
YOR*†:	0111bbrrrr	output & OR B with/to R
YAND*†:	0110bbrrrr	output & AND B with/to R
YXOR*†:	0101bbrrrr	output & XOR B with/to R
YASR*†:	000111rrrr	output & arith SR R to R
YLSL*†:	000110rrrr	output & logical SL R to R
Control Register Instructions		
RST:	0000000001	reset CR
DTCR:	0000101110	xfr D to CR
CRTD:	0000101111	xfr CR to D
SETI:	0000100iix	set cond re-init on CMP mode
SETP:	00001010pp	set chip precision
SETY:	00001001x	set Y port to trans/latched mode
SELR:	00001101x	select upper/lower R bank
SELB:	00001100x	select upper/lower B bank
SETU:	00001011x	set post/pre update mode
SETA:	00001010x	set cond AIR mode
AIR Instructions		
WRA:	0000101100	write AIR with D
RDA:	0000101101	read AIR at D
LDA:	0000111110	load AIR on next cycle
Misc. Instructions		
YDTY:	0000011111	pass D to Y port
YREV*†:	1001bbrrrr	output R in bit-reverse format
NOP:	0000000000	no operation

*External data may substitute for R using DSEL.

†Operable in either pre- or post-update mode.

Table 2. ADSP-1410 Instruction Set